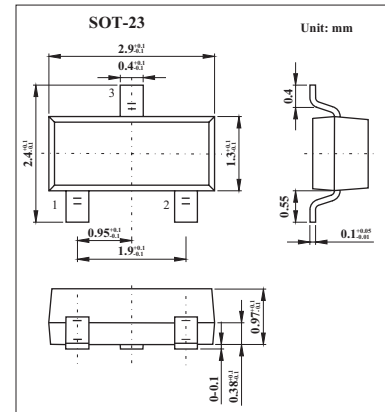


## BAS70 series

### ■ Features

- Low forward current
- High breakdown voltage
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	$V_R$			70	V
Continuous forward current	$I_F$			70	mA
Repetitive peak forward current	$I_{FRM}$	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		70	mA
Non-repetitive peak forward current	$I_{FSM}$	$t_p < 10 \text{ ms}$		100	mA
Storage temperature	$T_{stg}$		-65	+150	$^\circ\text{C}$
Junction temperature	$T_j$			150	$^\circ\text{C}$
Operating ambient temperature	$T_{amb}$		-65	+150	$^\circ\text{C}$
thermal resistance from junction to ambient	$R_{th\ j-a}$			500	K/W

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Max	Unit
Forward voltage	$V_F$	$I_F = 1 \text{ mA}$	410	mV
		$I_F = 10 \text{ mA}$	750	mV
		$I_F = 15 \text{ mA}$	1	V
Reverse voltage leakage current	$I_R$	$V_R = 50 \text{ V}; \text{ note 1}$	100	nA
		$V_R = 70 \text{ V}; \text{ note 1}$	10	$\mu\text{A}$
Charge carrier life time (Krakauer method)	$\tau$	$I_F = 5 \text{ mA}$	100	ps
Diode capacitance	$C_d$	$f = 1 \text{ MHz}; V_R = 0;$	2	pF

Note

1. Pulse test:  $t_p = 300 \mu\text{ s}; \delta = 0.02$

### ■ Marking

Type	BAS70	BAS70-04	BAS70-05	BAS70-06	BAS70-07
Marking	73*	74*	75*	76*	77p